

Gate driver AUIR3241S

LOW QUIESCENT CURRENT BACK TO BACK MOSFET DRIVER

Features

- Very low quiescent current on and off state
- Back to back configuration
- Boost converter with integrated diode
- Standard level gate voltage
- Input active high and 3.3V compatible
- Under voltage lockout with diagnostic
- Wide operating voltage 3-36V
- Ground loss protection
- Lead-Free, Halogen Free, RoHS compliant

Applications

- Power switch for Stop and Start board net stabilizer
- Battery switch

Product Summary

Operating voltage 3-36V Vgate 11.5V min. I Vcc average On 45µA max. at 25°C I Vcc average Off 35µA max. at 25°C

Package



Description

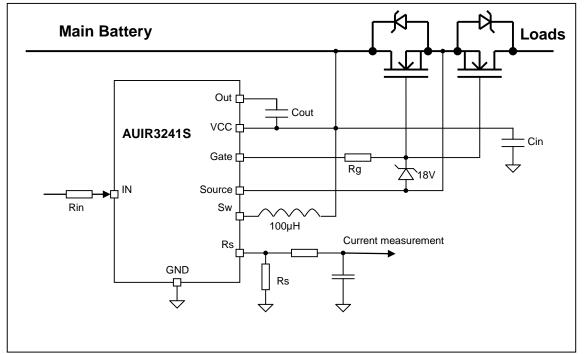
The AUIR3241S is a high side Mosfet driver for back to back topology targeting back to back switch. It features a very low quiescent current both on and off state. The AUIR3241S is a combination of a boost DC/DC converter using an external inductor and a gate driver. It drives standard level Mosfet even at low battery voltage. The input controls the gate voltage. The AUIR3241S integrates an under voltage lock out protection to prevent to drive the Mosfet in linear mode.

Ordering Information

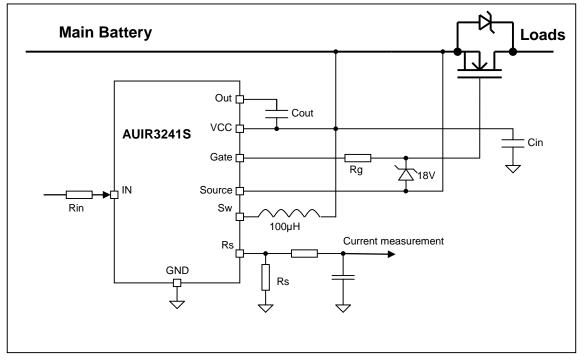
Base Part Number	Deskars Torre	Standard Pack Form Quantity		Ormalate Devi Nember
Dase Fart Number	Package Type			Complete Part Number
AUIR3241S	SOIC8	Tape and reel	2500	AUIR3241STR



Typical Connection – Back to Back

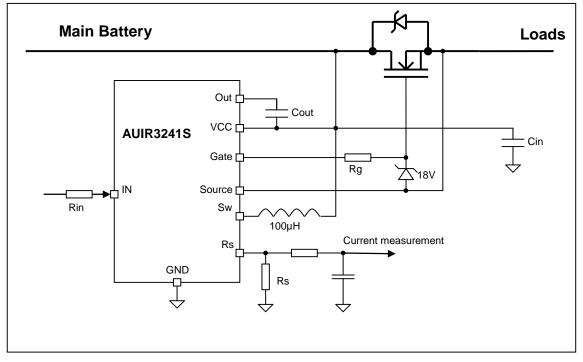


Typical Connection – Q_diode





Typical Connection – Battery switch





Absolute Maximum Ratings Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur.

Symbol	Parameter	Min.	Max.	Units
Vcc-gnd	Maximum Vcc voltage	-0.3	65	
Vsw-gnd	Maximum Sw voltage	Vrs-0.3	Vout+Vf	
Vsw-Vrs	Maximum Sw voltage	-0.3	65	
Vout-Vcc	Maximum Vout-Vcc voltage	-0.3	65	
Vout-gnd	Maximum Vout voltage	-0.3	65	V
Vout-Vgate	Maximum Vout-Vgate voltage	-0.3	65	v
Vgate-Vsource	Maximum Vgate-Vsource voltage	-0.3	75	
Vout-Vsource	Maximum Vout-Vsource voltage	-0.3	75	
Vrs-gnd	Maximum Rs pin voltage	-0.3	6	
Vin-gnd	Maximum IN pin voltage	-0.3	Vout+0.3	
Isw	Maximum continuous current in Sw pin	_	200	
ID	Maximum continuous current in the rectifier diode	_	200	mA
Rg	Minimum gate resistor	100	—	Ohm
	Maximum operating junction temperature	-40	150	°C
Tj max.	Maximum storage temperature	-55	150	-0

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
Rth	Thermal resistance junction to ambient	100		°C/W

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
VIH	High level input voltage	2.5	5.5	V
VIL	Low level input voltage	0	0.8	v



Static Electrical Characteristics

-40 125°C Vcc-6 16V (unless otherwise spe value are given for Vec-14V and Ti-25°C

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
	Supply voltage range for extended operation (some					
Vcc op (ext).	parameters may be downgraded beyond nominal	3		36	V	See page 11
	operation)					
Vcc op (nom). ⁽¹⁾	Supply voltage range for nominal operation	6	_	16		
Iq Vcc Off (2)	Supply current when Off, Tj=25°C	-	2	6		Vin=0V,K1/K2 off,
	Supply current when Off, Tj=125°C	_	3	8		K3 on, Vout-Vcc=14
lq Vcc On (2)	Supply current when On, Tj=25°C	_	3	6		Vin=5V,K1/K3 off,
	Supply current when On, Tj=125°C	_	4	8	μA	K2 on, Vout-Vcc=14
Iq Out Off ⁽²⁾	Quiescent current on Out pin, Tj=25°C	_	10	15		Vin=0V,K1/K2 off,
	Quiescent current on Out pin, Tj=125°C	_	13	25		K3 on, Vout-Vcc=14
lq Out On ⁽²⁾	Quiescent current on Out pin, Tj=25°C	_	12	20		Vin=5V,K1/K3 off,
	Quiescent current on Out pin, Tj=125°C	_	15	30		K2 on, Vout-Vcc=14
Vbr Out	Breakdown voltage between Out and Source	75	90	_		I=10mA
Vbr Gate	Breakdown voltage between Gate and Source	75	90	_	V	I=10mA
OV	Over-voltage protection between Vout and Gnd	50	55	62		
lin	Input current	_	3	6	μA	Vin=5V
Vin_th	Input voltage threshold	0.8	1.5	2.5		
Vout_th	Output voltage threshold	11.5	12.5	14		
UV_LO	Undervoltage lockout between Vout and Vcc	6.5	8	10	V	See figure 7
Vout_th–UV_LO	Output voltage minus Undervoltage lockout threshold	3	4.5	_		
Vrs th	Rs threshold	0.8	1	1.3		
I latch UV_LO	Under voltage lockout Latch current between Vout and	10	25	40		See page 11
	Vcc				mA	
Vf	Forward voltage of rectifier diode	_	0.9	1.1	V	I=100mA, Tj=25°C
Rdson K1	Rdson of K1, Tj=-40°C	_	8	13		I=100mA,
	Rdson of K1, Tj=25°C	_	11	15	1	Vout-Vcc=12.5V
	Rdson of K1, Tj=125°C	_	15	20	Ω	
Rdson K2	Rdson of K2, Tj=25°C	_	25	_]	I=100mA
Rdson K3	Rdson of K3, Tj=25°C		25	_]	

⁽¹⁾ If the part is supply outside of this range (ex: during ramp up of Vcc), other values in this table might not be guaranteed ⁽²⁾ Supply current might be higher than specified during the start-up of the part (especially during the charge of Cout)

Timing Converter Characteristics <u>Tj=-40..125°C</u>, Vcc=6..16V (unless otherwise specified), typical value are given for Vcc=14V and Tj=25°C.

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
Toff	Off time	2	3	4		See figure 4
Tdon K1	Turn-on delay of K1	_	5	_		See figure 5
Tdoff K1	Turn-off delay of K1	_	0.2	_	μs	See ligule 5
POR_Delay	Power On Reset delay	200	500	1200		See figure 10
POR_Th	Power On Reset threshold	6	6.5	7.5	V	

Switching Characteristics <u>Tj=-40..125°C</u>, Vcc=6..16V (unless otherwise specified), typical value are given for Vcc=14V and Tj=25°C.

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
Tdon gate	Turn-on delay	0.5	1.5	3		
Tr gate	Rise time on gate 10% to 90% of Vout-Vcc	—	6	15	μs	Cgate=100nF
lgate+	Gate high short circuit pulsed current	100	350		mA	Vgate-Vsource=0V
Tdoff gate	Turn-off delay	0.5	2	5		
Tf gate	Fall time on gate 90% to 10% of Vout-Vcc	—	6	15	μs	Cgate=100nF
Igate-	Gate low short circuit pulsed current	100	350	_	mA	Vgate-Vsource=14V
Treset	Time to reset the under voltage latches	—	1	100	μs	See page 11



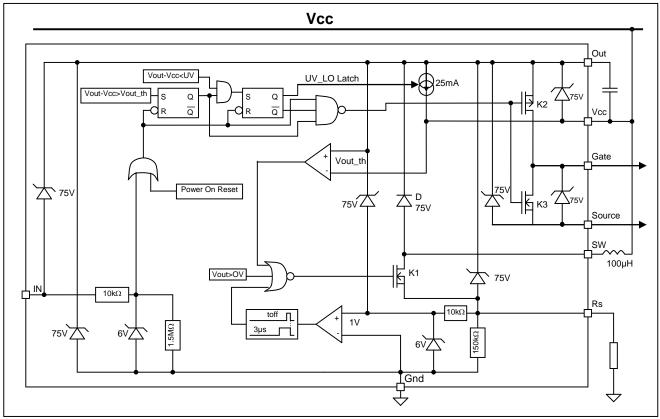
Lead Definitions

Pin number	Symbol	Description
1	IN	Input pin
2	GND	Ground pin
3	RS	Current sense input pin
4	SW	Output of K1
5	Source	Connection of the source pin of the Mosfets
6	Gate	Output of the gate driver
7	Vcc	Power supply
8	Out	Output of the boost converter

Lead Assignments



Block diagram



Input Circuitry

The input control circuitry drives the output gate driver stage. The input is active high. With a low level input voltage, the gate is shorted to the source. With a high level input, the output gate driver turn on when Vout reaches Vout_th.

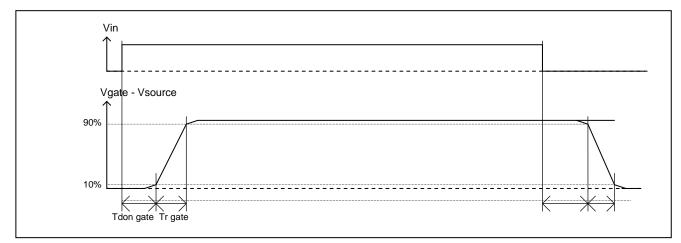


Figure 1

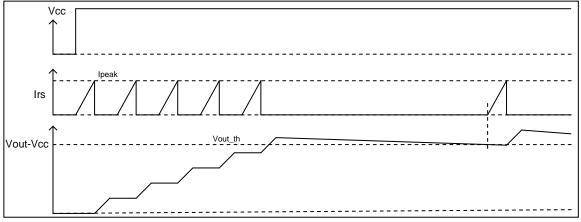
7



Description

The topology of the AUIR3241S is a boost DC/DC converter working in current mode. The DC/DC is working once the AUIR3241S is powered regardless the input level.

K1 is switched on when the gate voltage is lower than Vout threshold. When Rs pin reaches Vrs th, K1 is turned off and the inductor charges the Out capacitor through D. The system cannot restart during Toff after Vrs th has been reached. The DC/DC restart only when the Out and the Vcc voltage difference is lower than Vout_th in order to achieve low quiescent current on the power supply. To turn off the power Mosfet, the input must be low. Then K2 is turned off and K3 shorts the gate to the source.





Parameters definition

Current definition

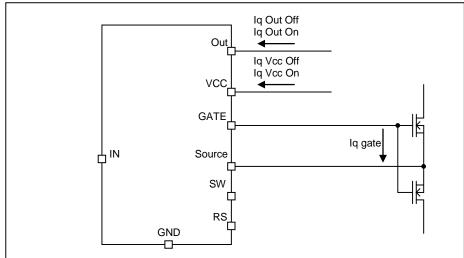


Figure 3



Timing definition

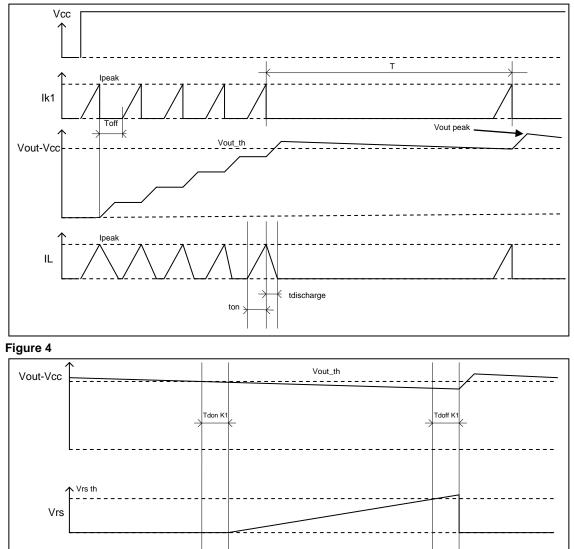


Figure 5

Low quiescent current operation when On.

The AUIR3241S is able to operate with a very low quiescent current on the Vcc pin. Nevertheless the supply current depends also on the leakage of the power mosfet named "Iq gate" on the diagram below.

The leakage current is given when K1 is off. When K1 is on, the current flowing in Vcc is the current charging the inductor. Therefore the average current on the Vcc is the combination of the current when K1 is ON and OFF. The average current on the Vcc pin can be calculated using:

 $I \text{ Vcc average on} = (Iq \text{ gate} + Iq \text{ Out On}) * \frac{Vout - Vcc + Vf}{Vcc} + Iq \text{ Vcc on} + Iq \text{ Out on}$ $I \text{ Vcc average off} = (Iq \text{ gate} + Iq \text{ Out Off}) * \frac{Vout - Vcc + Vf}{Vcc} + Iq \text{ Vcc off} + Iq \text{ Out off}$

With Vout: the average voltage on the output. Vout average = (Vout peak + Vout th)/2

Vout peak can be calculated by:

Vout peak = $\sqrt{\frac{L}{Cout}}$. Ipeak² + Vout th²



During On operation, the DC/DC works in pulse mode, meaning each time the Vout-Vcc voltage comes below 12.5V, the AUIR3241S switches on K1 to recharge the gate voltage. When the lout leakage is low enough to maintain the DC/DC in discontinuous mode, the frequency is calculate by:

$$T = \frac{Ipeak^{2}*L}{2*(Iq gate+Iq Vout on)*(Vout-Vcc+Vf)}$$

Peak current control

The current in the inductor is limited by the 1V comparator which monitors the voltage across Rs. Due to the delay in the loop (tdoff K1), the inductor current will exceed the threshold set by: $\frac{Vrsth}{Rs}$

At low voltage, the current waveform in the inductor is not anymore linear, but exponential because the sum of the resistor of K1, the inductor and RS are not any more negligible.

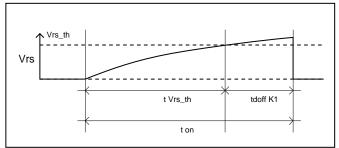


Figure 6

The peak current and ton can be calculated as follow:

 $t Vrsth = -\frac{L}{Rdon k1 + Rs + Rl} * ln(1 - \frac{Rs + Rdson k1 + Rl}{Vrs_th * Rs * Vcc})$ Where RI is the resistor of the inductor

With : $t on = t Vrs_th + tdoff K1$

The peak current can be solved by:

 $Ipeak = \frac{Vcc}{Rdson k1 + Rs + Rl} * (1 - e^{-ton*\frac{Rdson k1 + Rs + Rl}{L}})$

The peak current must not exceed the Maximum Rating of Isw.



Output capacitor choice

Mosfet.

The output capacitor must be chosen based on 2 criteria:

- During the turn on of K2, the voltage drop on Cout must not trigger the Under Voltage Lockout due to the gate charge of the Power

 $Cout > \frac{Q \text{ gate total Power Mosfet}}{(Vout_{th} - UV_{LO}) \text{ Min.}}$

- When K1 turn off and the inductor is charging Cout, the peak current on the output capacitor must be limited in order to avoid having current flowing in the Gate zener diode:

 $Cout > \frac{L * Ipeak^2 max}{Vz \min gate^2 - Vout th max^2}$

Vz min gate is the minimum Zener voltage of the external gate Zener diode.

Minimum operating voltage

While the AUIR3241S operating voltage is specified between 3V and 36V. The 3V minimum operating voltage is when the Vcc is going down. The minimum voltage is also limited by the fact that the Rs voltage must reach the Vrsth taking account all resistors which limit the inductor current.

 $Vcc min = \frac{Rdson k1 + Rs + Rl}{Rs} * Vrsth$

Over-Voltage protection

The AUIR3241S integrates an over-voltage protection in order to protect K1. When Vcc exceed the Over-voltage threshold, the DC/DC is stopped.

Under voltage lockout - Diagnostic

In order to avoid to drive the Power Mosfet in linear mode, the AUIR3241S features an under voltage lockout. During the turn on, the gate will not be powered until Vout-Vcc reaches Vout th, meaning K2 is off and K3 is on. Then the AUIR3241S powers the gate of the mosfet. If Vout-Vcc goes below UV_LO, the gate is shorted to the source and the part is latched. A cycle in the input is required to reset the latch. The input must be kept low longer than Treset.

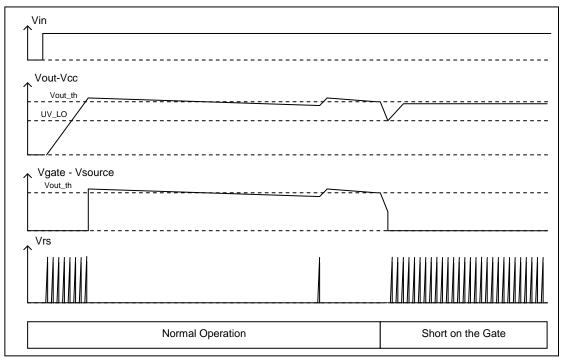


Figure 7

When the part is latched a current source (I latch UV_LO) is connected between Out and Vcc to increase the current consumption. By monitoring the current consumption the system can have a diagnostic of the output status. The diagnostic can be analog or digital.

infineon

Analog Diagnostic: Output current measurement

The average current into Rs can be measured by adding a low pass filter before the ADC of the micro controller.

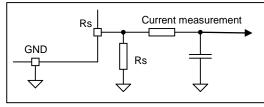


Figure 8

Then the average output current can be evaluated using :

l out av = I Rs av * Vcc / (Vout - Vcc)

Knowing the output current can be useful to do a diagnostic on the power Mosfet. If the gate is shorted, the output current will be significantly higher than in normal operation.

Digital diagnostic

By adding a diode during high current consumption mode, the output voltage can be close to 1V. Using a bipolar with a pull-up resistor will provide a digital diagnostic.

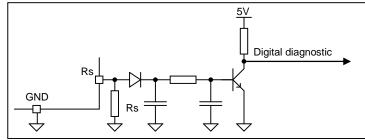
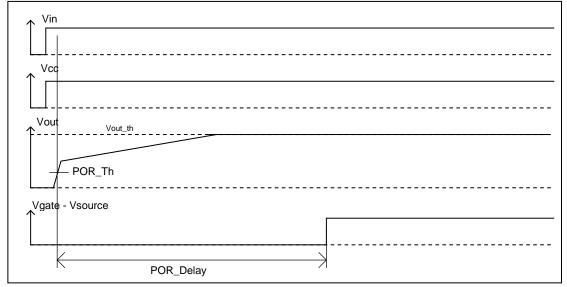


Figure 9

Power On Reset

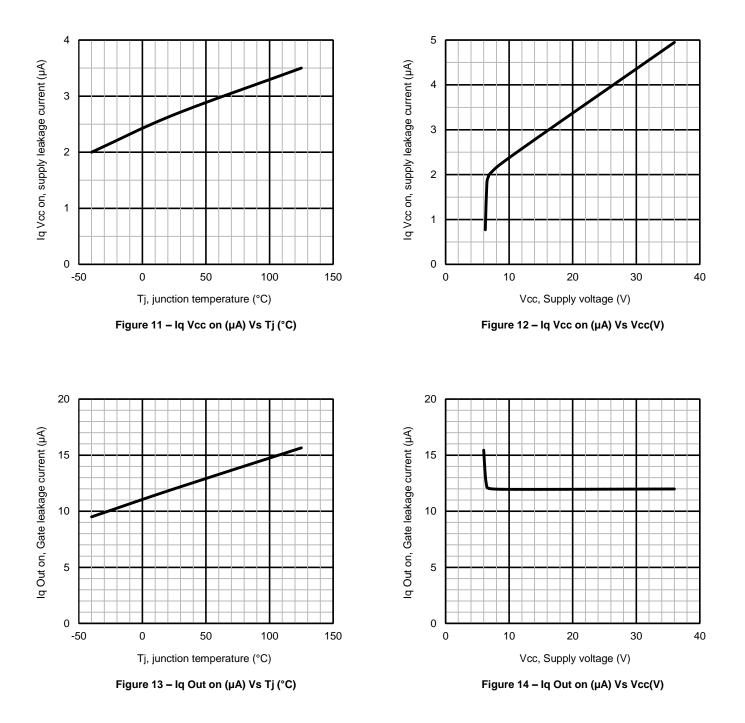
During the power on, the AUIR3241S features a Power On Reset to guarantee a stable state of the 2 latches of the Under voltage lockout and guarantee a stable internal biasing. POR_Delay is triggered when Vout-Gnd exceeds POR_Th.





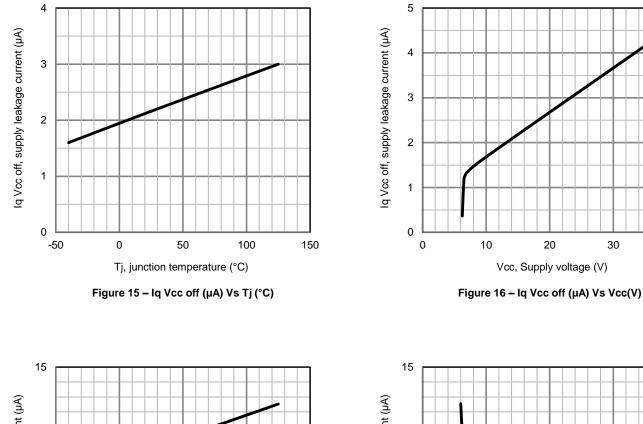


Figures are given for typical value, Vcc=14V and Tj=25°C otherwise specified





40



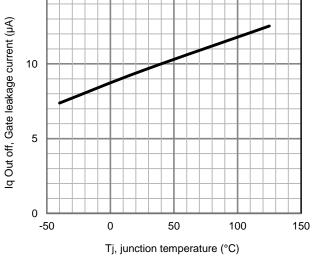


Figure 17 – Iq Out off (μA) Vs Tj (°C)

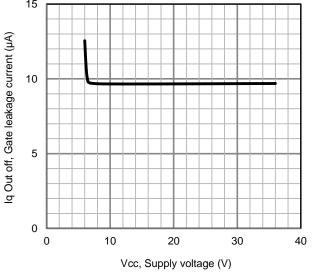
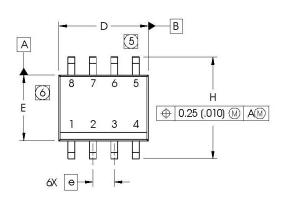


Figure 18 – Iq Out off (µA) Vs Vcc(V)

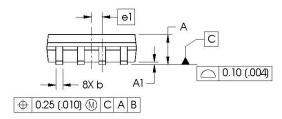


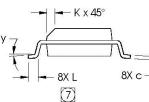
Case Outline – SO8

Dimensions are shown in millimeters (inches)

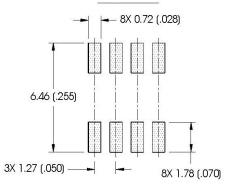


	INC	HES	MILLIN	METERS	
DIM	MIN	MAX	MIN	MAX	
А	.0532	.0688	1.35	1.75	
A1	.0040	.0098	0.10	0.25	
b	.013	.020	0.33	0.51	
С	.0075	.0098	0.19	0.25	
D	.189	.1968	4.80	5.00	
Е	.1497	.1574	3.80	4.00	
е	.050 B.	ASIC	1.27 BASIC		
e1	.025 B.	ASIC	0.635	BASIC	
Н	.2284	.2440	5.80	6.20	
Κ	.0099	.0196	0.25	0.50	
L	.016	.050	0.40	1.27	
y	0°	8°	0°	8°	





FOOTPRINT



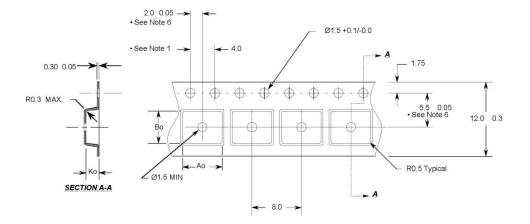
NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- 5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- 6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

15 Rev 1.01



Tape & Reel **SO8**



 Notes:
 0.2

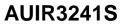
 2. Camber not to exceed 1mm in 100mm
 0.2

 3. Material: Black Conductive Advantek Polystyrene
 4. Ao and Bo measured on a plane 0.3mm above the bettern of the product

Ao and Bo measured on a plane 0.3mm above the bottom of the pocket
 Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
 Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

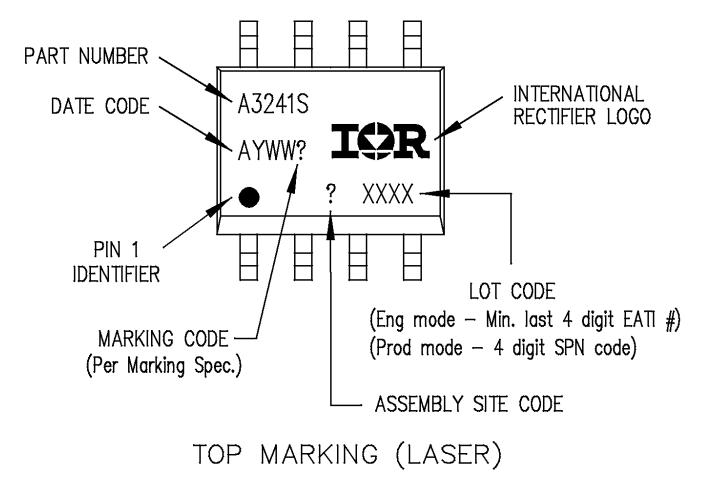
- Ao = 6.4 mm Bo = 5.2 mm Ko = 2.1 mm
- All Dimensions in Millimeters -

16 Rev 1.01





Part Marking Information



Qualification Information

Qualification Level		Automotive (per AEC-Q100) Comments: This family of ICs has passed an Automotiv qualification. IR's Industrial and Consumer qualification lev is granted by extension of the higher Automotive level.				
Moisture Sensitivit	y Level	SOIC-8L	MSL2, 260°C (per IPC/JEDEC J-STD-020)			
ESD	Human Body Model	Class 1C Passed 1500V (per AEC-Q100-002)				
Charged Device Model		Class C6 (+/-1000V) (per AEC-Q100-011)				
IC Latch-Up Test		Class II Level A (per AEC-Q100-004)				
RoHS Compliant		N. N.	Yes			



Published by Infineon Technologies AG 81726 München, Germany © Infineon Technologies AG 2015 All Rights Reserved.

IMPORTANT NOTICE

The information given in this document shall in <u>no event</u> be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (<u>www.infineon.com</u>).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may <u>not</u> be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.



Revision History

Revision	Date	Notes/Changes	
Rev 1.0	2017-04-27	Data Sheet created.	
Rev 1.01	2017-09-12	Update drawing, Differentiate Vcc_op (ext) & Vcc_op (nom), add Appendixies (1) & (2) on Page 5	



单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon Technologies(英飞凌)